RTL8189ES-VB-CG

SINGLE-CHIP IEEE 802.11b/g/n 1T1R WLAN WITH SDIO INTERFACE

DATASHEET
(CONFIDENTIAL: Development Partners Only)

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USING THIS DOCUMENT

This document is intended for the software engineer's reference and provides detailed programming information.

Though every effort has been made to ensure that this document is current and accurate, more information may have become available subsequent to the production of this guide.

REVISION HISTORY

Revision	Release Date	Summary
1.0	2012/12/25	First release

Table of Contents

List of Tables

List of Figures

1. General Description

The Realtek RTL8189ES-VB-CG is a highly integrated single-chip 802.11n Wireless LAN (WLAN) network SDIO interface (SDIO 1.1/ 2.0/ 3.0 compliant) controller. It is a WLAN MAC, a 1T1R capable WLAN baseband, and WLAN RF in a single chip. The RTL8189ES-VB provides a complete solution for a high-throughput performance integrated wireless LAN device.

The RTL8189ES-VB WLAN baseband implements Orthogonal Frequency Division Multiplexing (OFDM) with 1 transmit and 1 receive path and is compatible with the IEEE 802.11n specification. Features include one spatial stream transmission, short guard interval (GI) of 400ns, spatial spreading, and transmission over 20MHz and 40MHz bandwidth.

For legacy compatibility, Direct Sequence Spread Spectrum (DSSS), Complementary Code Keying (CCK) and OFDM baseband processing are included to support all IEEE 802.11b and 802.11g data rates. Differential phase shift keying modulation schemes, DBPSK and DQPSK with data scrambling capability, are available, and CCK provides support for legacy data rates, with long or short preamble. The high-speed FFT/IFFT paths, combined with BPSK, QPSK, 16QAM, and 64QAM modulation of the individual subcarriers and rate compatible punctured convolutional coding with coding rate of 1/2, 2/3, 3/4, and 5/6, provide higher data rates of 54Mbps and 150Mbps for IEEE 802.11g and 802.11n OFDM respectively.

The RTL8189ES-VB WLAN Controller builds in an enhanced signal detector, an adaptive frequency domain equalizer, and a soft-decision Viterbi decoder to alleviate severe multi-path effects and mutual interference in the reception of multiple streams. Robust interference detection and suppression are provided to protect against Bluetooth, cordless phone, and microwave oven interference.

Efficient IQ-imbalance, DC offset, phase noise, frequency offset, and timing offset compensations are provided for the radio frequency front-end. Selectable digital transmit and receive FIR filters are provided to meet transmit spectrum mask requirements and to reject adjacent channel interference, respectively.

The RTL8189ES-VB WLAN Controller supports fast receiver Automatic Gain Control (AGC) with synchronous and asynchronous control loops among antennas, antenna diversity functions, and adaptive transmit power control function to obtain the better performance in the analog portions of the transceiver.

The RTL8189ES-VB WLAN MAC supports 802.11e for multimedia applications, 802.11i for security, and 802.11n for enhanced MAC protocol efficiency. Using packet aggregation techniques such as A-MPDU with BA and A-MSDU, protocol efficiency is significantly improved. Power saving mechanisms such as Legacy Power Save, and U-APSD, reduce the power wasted during idle time, and compensates for the extra power required to transmit OFDM. The RTL8189ES-VB provides simple legacy and 20MHz/40MHz co-existence mechanisms to ensure backward and network compatibility.

2. Features

General

- 32-pin QFN

- CMOS MAC, Baseband PHY, and RF in a single chip for IEEE 802.11b/g/n compatible WLAN

- Complete 802.11n solution for 2.4GHz band

- 72.2Mbps receive PHY rate and 72.2Mbps transmit PHY rate using 20MHz bandwidth

- 150Mbps receive PHY rate and 150Mbps transmit PHY rate using 40MHz bandwidth

- Compatible with 802.11n specification

- Backward compatible with 802.11b/g devices while operating in 802.11n mode

Host Interface

- Complies with SDIO 1.1/ 2.0/ 3.0 for WLAN with clock rate up to 100MHz

- GSPI interface for configurable endian for WLAN

Standards Supported

- IEEE 802.11b/g/n compatible WLAN

- IEEE 802.11e QoS Enhancement (WMM)

- 802.11i (WPA, WPA2). Open, shared key, and pair-wise key authentication services

WLAN MAC Features

- Frame aggregation for increased MAC efficiency (A-MSDU, A-MPDU)

- Low latency immediate High-Throughput Block Acknowledgement (HT-BA)

- PHY-level spoofing to enhance legacy compatibility

- Power saving mechanism

- Channel management and co-existence

- Transmit Opportunity (TXOP) Short Inter-Frame Space (SIFS) bursting for higher multimedia bandwidth

WLAN PHY Features

- IEEE 802.11n OFDM

- One Transmit and one Receive path (1T1R)

- 20MHz and 40MHz bandwidth transmission

- Short Guard Interval (400ns)

- DSSS with DBPSK and DQPSK, CCK modulation with long and short preamble

- OFDM with BPSK, QPSK, 16QAM, and 64QAM modulation.
  Convolutional Coding Rate: 1/2, 2/3, 3/4, and 5/6

- Maximum data rate 54Mbps in 802.11g and 150Mbps in 802.11n

- Switch diversity for DSSS/CCK

- Hardware antenna diversity on per packet base

- Selectable receiver FIR filters

- Programmable scaling in transmitter and receiver to trade quantization noise against increased probability of clipping

- Fast receiver Automatic Gain Control (AGC)

- On-chip ADC and DAC

Peripheral Interfaces

- General Purpose Input/Output (8 pins)

- One configurable LED pin

3.   System Applications
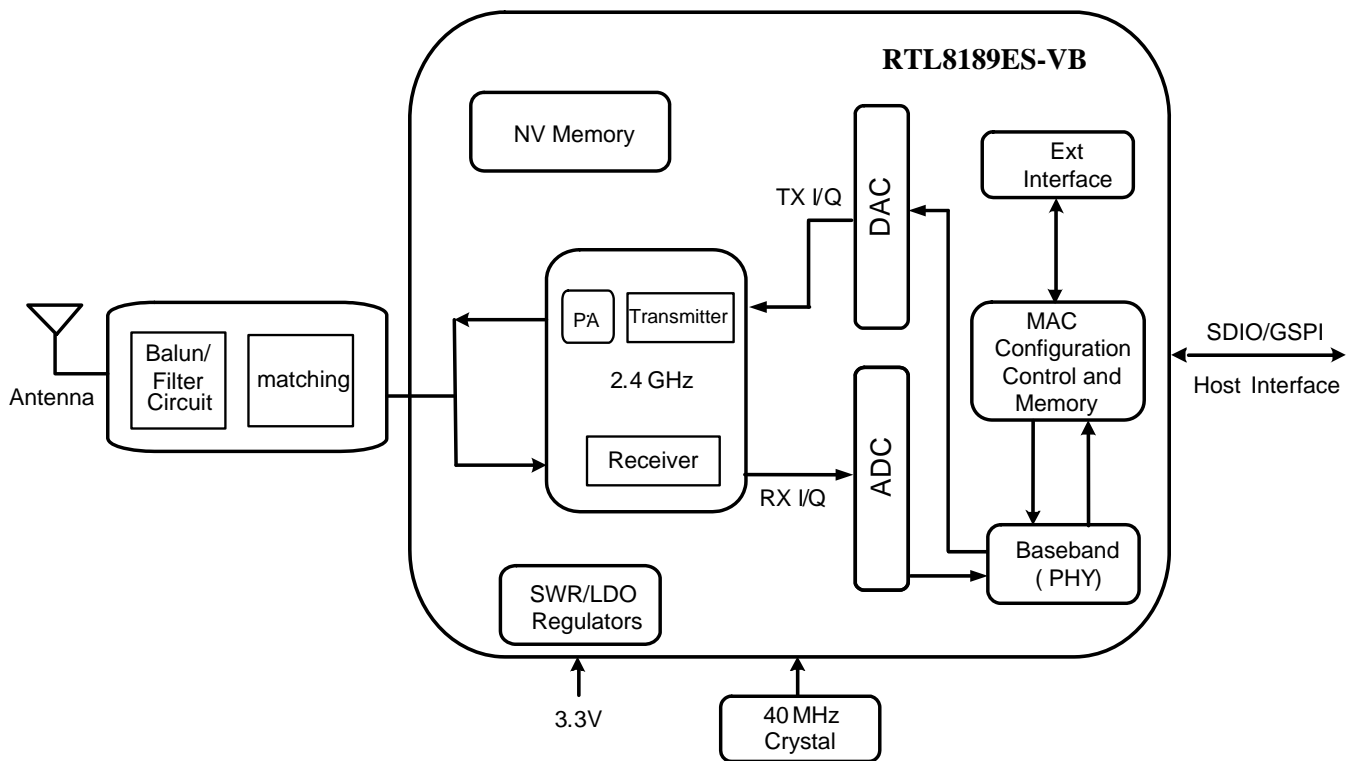
3.1. Single-Band 11n (1x1) Solution

Figure 1.   Single-Band 11n (1x1) Solution

4. Pin Assignments
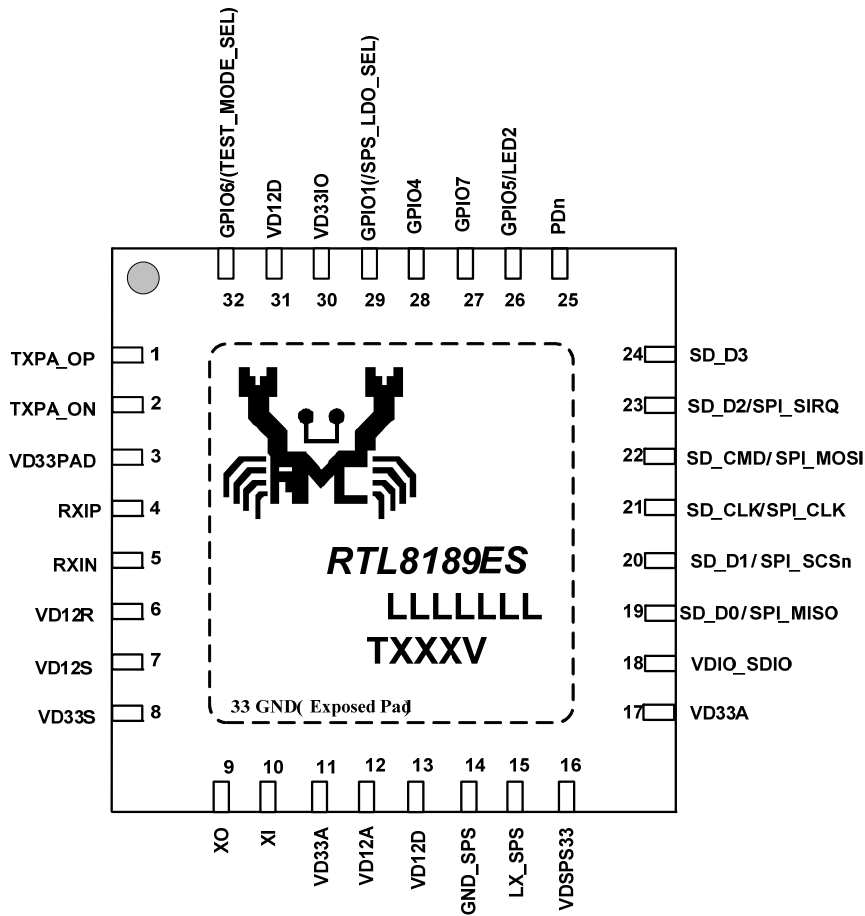
Figure 2. Pin Assignments

4.1. Package Identification

'Green' package is indicated by a 'G' in the location marked 'T' in Figure 2Figure 2. The version is shown in the location marked 'V', e.g.,.B=Version B.

5. Pin Descriptions

The following signal type codes are used in the tables:

    I: Input   O: Output

    T/S: Tri-State Bi-Directional Input/Output Pin   S/T/S: Sustained Tri-State

    O/D: Open Drain   P: Power Pin

5.1. SDIO Interface

Table 1. SDIO Interface

Symbol	Type	Pin No	Description
SD_CLK	I	21	SDIO Clock Input
SD_CMD	I/O	22	SDIO Command Input
SD_D0	I/O	19	SDIO Data Line 0
SD_D1	I/O	20	SDIO Data Line 1
SD_D2	I/O	23	SDIO Data Line 2
SD_D3	I/O	24	SDIO Data Line 3

Note: For details of SDIO interface selection, see section 6.4.2 SDIO/GSPI Interface Signal Level, page 10.

5.2. GSPI Interface

Table 2. GSPI Interface

Symbol	Type	Pin No	Description
SPI_CLK	I	21	GSPI Clock Input
SPI_MOSI	I	22	GSPI Data Input
SPI_MISO	O	19	GSPI Data Out
SPI_SIRQ	O	23	GSPI Interrupt
SPI_SCSn	I	20	GSPI Chip Select Bar

Note: The GSPI interface pins are shared with the SDIO interface. For details of SDIO interface selection, see section 6.4.2 SDIO/GSPI Interface Signal Level, page 10.

5.3. Power Pins

Table 3. Power Pins

Symbol	Type	Pin No	Description
LX_SPS	P	15	Switching Regulator Output
VDSPS33	P	16	Switching Regulator Input or Linear Regulator output from 3.3V to 1.5V
VD33A	P	11, 17	VDD 3.3V for Analog
VD33IO	P	30	VDD3.3V for Digital
VD33PAD	P	3	VDD 3.3V for PAD
VD33S	P	8	VDD 3.3V for Analog
VDIO_SDIO	P	18	VDD for SDIO Pin. The power supply is the same as the signal level of SDIO bus (3.3V ~ 1.8V)
VD12A	P	12	VDD 1.2V for Analog
VD12D	P	13, 31	VDD 1.2V for Digital
VD12R	P	6	VDD 1.2V for Analog
VD12S	P	7	VDD 1.2V for Analog
GND_SPS	P	14	Switching Regulator Ground

5.4. RF Interface

Table 4. RF Interface

Symbol	Type	Pin No	Description
RXIN	I	5	RF RX Negative Signal
RXIP	I	4	RF RX Positive Signal
TXPA_ON	O	2	RF TX Negative Signal
TXPA_OP	O	1	RF TX Positive Signal

5.5. LED Interface

Table 5. LED Interface

Symbol	Type	Pin No	Description
LED2	O	26	LED pin (Active Low). This pin is shared with GPIO5. It can be selected via the control register

5.6. Clock and Other Pins

Table 6. Clock and Other Pins

Symbol	Type	Pin No	Description
XI	I	10	OSC Input.
			Input of Crystal Clock Reference.
			The Crystal Clock can be 40MHz, 13MHz, 19.2MHz, 20MHz, 25MHz, 26MHz, 38.4MHz, 17.664MHz, 16MHz, 14.318MHz, or 12MHz
XO	O	9	Output of Crystal Clock Reference
PDn	I	25	This pin can Externally Shutdown the RTL8189ES-VB without requiring an extra power switch
CLK_REQ	O	26	This pin is used by the RTL8189ES to request the system clock from the host. It is shared with GPIO5. It can be selected via the control register
GPIO1/(SPS_LDO_SEL)	IO	29	.General Purpose Input/Output Pin.
			Trap function: weakly pull low to enable the integrated switching regulator; weakly pull high to enable the integrated linear regulator
GPIO4	IO	28	General Purpose Input/Output Pin
GPIO5	IO	26	General Purpose Input/Output Pin. This pin is shared with CLK_REQ and LED2.
GPIO6/(TEST_MODE_SEL)	IO	32	General Purpose Input/Output Pin.
			Trap function: weakly pull low to enable the RTL8189ES-VB to enter normal operation mode.
GPIO7	IO	27	General Purpose Input/Output Pin

6. Electrical and Thermal Characteristics

6.1. Temperature Limit Ratings

Table 7.   Temperature Limit Ratings

Parameter	Minimum	Maximum	Units
Storage Temperature	-55	+125	°C
Ambient Operating Temperature	0	70	°C
Junction Temperature	0	125	°C

6.2. Temperature Limit Ratings

Table 8.   Temperature Limit Ratings

Parameter	Minimum	Maximum	Units
Storage Temperature	-55	+125	°C
Ambient Operating Temperature	0	70	°C
Junction Temperature	0	125	°C

6.3. DC Characteristics

6.3.1. Power Supply Characteristics

Table 9.   DC Characteristics

Symbol	Parameter	Minimum	Typical	Maximum	Units
VD33A, VD33D	3.3V I/O Supply Voltage	3.0	3.3	3.6	V
VD12A, VD12D	1.2V Core Supply Voltage	1.10	1.2	1.32	V
IDD33	3.3V Rating Current	-	-	600	mA

6.3.2. Digital IO Pin DC Characteristics

Table 10. 3.3V GPIO DC Characteristics

Symbol	Parameter	Minimum	Normal	Maximum	Units
V$_{IH}$	Input High Voltage	2.0	3.3	3.6	V
V$_{IL}$	Input Low Voltage	--	0	0.9	V
V$_{OH}$	Output High Voltage	2.97	--	3.3	V
V$_{OL}$	Output Low Voltage	0	--	0.33	V

Table 11. 2.8V GPIO DC Characteristics

Symbol	Parameter	Minimum	Normal	Maximum	Units
V$_{IH}$	Input High Voltage	1.8	2.8	3.1	V
V$_{IL}$	Input Low Voltage	--	0	0.8	V
V$_{OH}$	Output High Voltage	2.5	--	3.1	V
V$_{OL}$	Output Low Voltage	0	--	0.28	V

Table 12. 1.8V GPIO DC Characteristics

Symbol	Parameter	Minimum	Normal	Maximum	Units
V$_{IH}$	Input High Voltage	1.7	1.8	2.0	V
V$_{IL}$	Input Low Voltage	--	0	0.8	V
V$_{OH}$	Output High Voltage	1.62	--	1.8	V
V$_{OL}$	Output Low Voltage	0	--	0.18	V

6.4. AC Characteristics

6.4.1. SDIO/GSPI Interface Timing
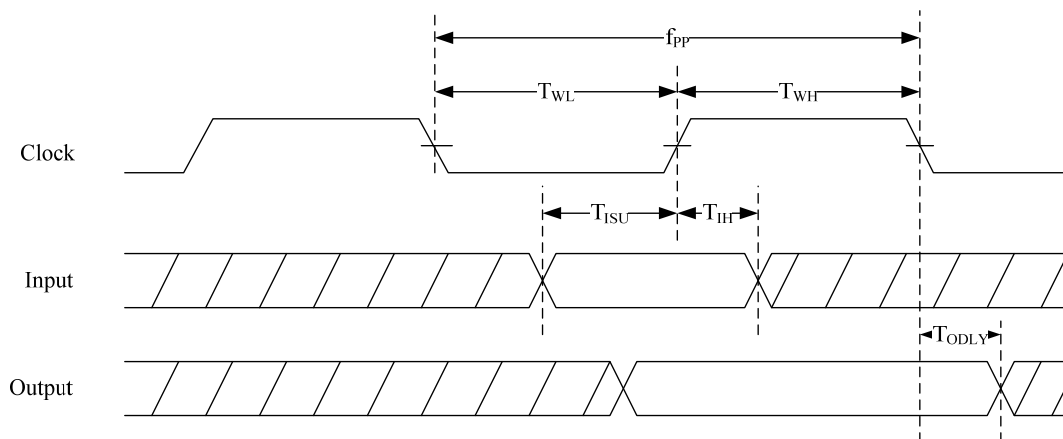
Figure 3.   SDIO/GSPI Interface Timing

Table 13. SDIO/GSPI Interface Timing Parameters

| NO	Parameter	Mode	MIN	MAX	Unit
f_{PP}	Clock Frequency	Default	0	25	MHz
		HS	0	50	MHz
T_{WL}	Clock Low Time	DEF	10	-	ns
		HS	7	-	ns
T_{WH}	Clock High Time	DEF	10	-	ns
		HS	7	-	ns
T_{ISU}	Input Setup Time	DEF	5	-	ns
		HS	6	-	ns
T_{IH}	Input Hold Time	DEF	5	-	ns
		HS	2	-	ns
T_{ODLY}	Output Delay Time	DEF	-	14	ns
		HS	-	14	ns

6.4.2. SDIO/GSPI Interface Signal Level

The SDIO and GSPI signal level ranges from 1.8V to 3.3V.

The DC characteristics of a typical signal level, 3.3V/2.8V/1.8V are shown in section 6.3.2 Digital IO Pin DC Characteristics, page 9.

6.4.3. SDIO Interface Power-On Sequence

After power-on, the SDIO interface is selected by the RTL8189ES-VB automatically when a valid SDIO command is received. To attain better SDIO host compatibility, the following power-on sequence is recommended:
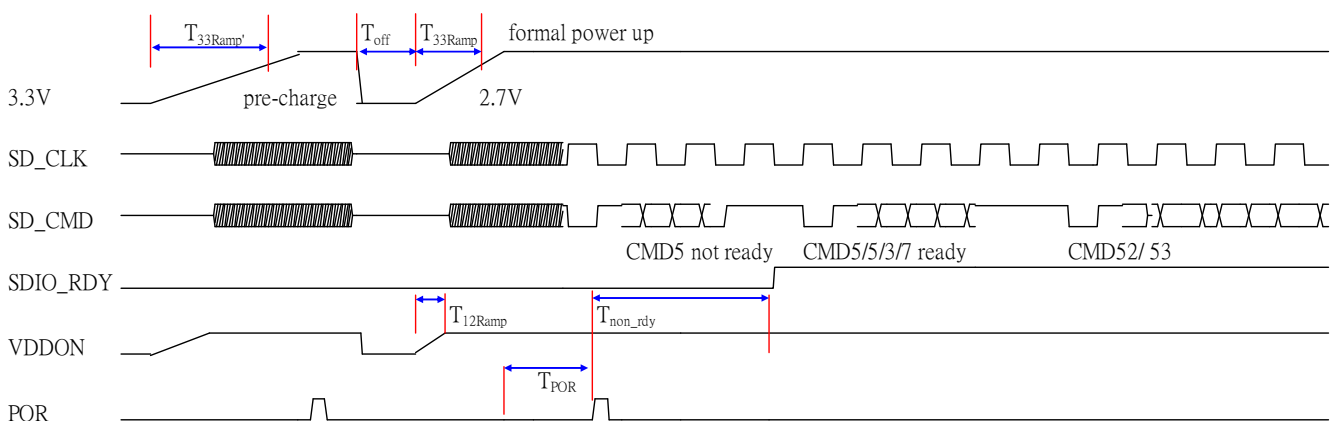
Figure 4. SDIO Interface Power-On Sequence

Definitions

$T_{33ramp'}$: The 3.3V power pre-charge ramp up duration before formal power up. We recommend that a 3.3V power-on and then power-off sequence is executed by the host controller before the formal power-on sequence. This procedure can eliminate the host card detection issue when the power ramp up duration is too long or the system warm reboot fails.

T_{off} : The duration 3.3V is cut off before formal power up.

T_{33ramp}: The 3.3V main power ramp up duration.

T_{12ramp}: The internal 1.2V ramp up duration.

T_{POR}: The duration the power-on reset releases, and the power management unit executes power-on tasks. The power-on reset will detect both 3.3V and 1.2V power ramp up after a predetermined duration.

T_{non_rdy}: SDIO not ready duration. In this state the RTL8189ES may respond to commands without the ready bit set. After the ready bit is set, the host will initiate the full card detection procedure.

Power-On Flow Description

We recommend that the card detection procedures are divided into two phases: a 3.3V power pre-charge phase and a formal power-up phase.

For the 3.3V power pre-charge phase, the power ramp up duration is not limited. The 3.3V is then cut off and is turned on after a T_{off} period. The ramp up time is specified by the T_{33ramp} duration.

After main 3.3V ramp up and 1.2V ramp up, the power management unit will be enabled by the power ready detection circuit, and will enable the SDIO block. eFUSE is then autoloaded to the SDIO circuits during the T_{non_rdy} duration. After the autoload has completed, the SDIO sets the ready bit. After CMD5/ 5/3/7 procedures, card detection is then executed. After the driver has loaded, normal commands 52 and 53 are then used.

A typical timing specification is shown below:

Table 14. SDIO Interface Power-On Timing Parameters

Parameter	Min	Typical	Max	Unit
$T_{33ramp'}$	-	-	No Limit	ms
T_{off}	250	500	1000	ms
T_{33ramp}	0.1	0.5	2.5	ms
T_{12ramp}	0.1	0.5	1.5	ms
T_{por}	2	2	8	ms
$T_{non-rdy}$	1	2	10	ms

6.4.4. GSPI Interface Power-On Sequence

The GSPI interface is enabled automatically when a valid GSPI command is first received. The recommended power-on sequence is as follows:
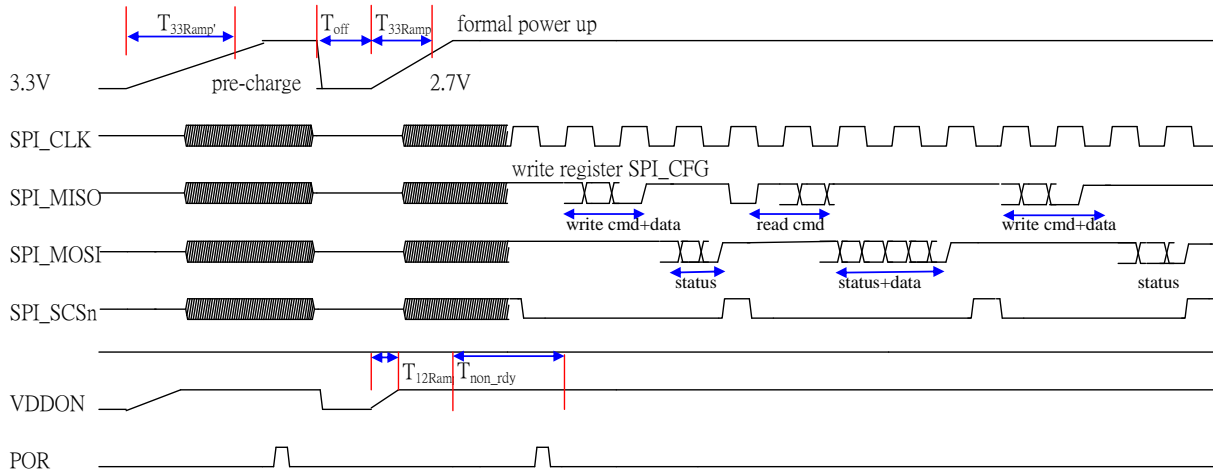

Figure 5.   GSPI Interface Power-On Sequence

Definitions

$T_{33ramp'}$: The 3.3V power pre-charge ramp up duration before formal power up. We recommend that a 3.3V power-on and then power-off sequence is executed by the host controller before the formal power-on sequence. This procedure can eliminate the host card detection issue when the power ramp up duration is too long or the system warm reboot fails.

T_{off} : The duration 3.3V is cut off before formal power up.

T_{33ramp}: The 3.3V main power ramp up duration.

T_{12ramp}: The internal 1.2V ramp up duration.

T_{non_rdy}: The duration of SPI device internal initialization. After T_{non_rdy}, the SPI host can then send commands to write the SPI_CFG register. The SPI_CFG register controls SPI endian and word length.

Power-On Flow Description

We recommend that the card detection procedures are divided into two phases: a 3.3V power pre-charge phase and a formal power-up phase.

For the 3.3V power pre-charge phase, the power ramp up duration is not limited. The 3.3V is then cut off and is turned on after a T_{off} period. The ramp up time is specified by the T_{33ramp} duration.

After main 3.3V ramp up and 1.2V ramp up, the power management unit will be enabled by the power ready detection circuit, and will enable the SPI block. eFUSE is then autoloaded to the SPI circuits, and the internal power circuits are configured during the T_{non_rdy} duration.

A typical timing specification is shown below:

Table 15. GSPI Interface Power-On Timing Parameters

Parameter	Min	Typical	Max	Unit
$T_{33ramp'}$	-	-	No Limit	ms
T_{off}	250	500	1000	ms
T_{33ramp}	0.1	0.5	2.5	ms
T_{12ramp}	0.1	0.5	1.5	ms
$T_{non-rdy}$	3	4	18	ms

7.   Mechanical Dimensions

TOP VIEW

BOTTOM VIEW
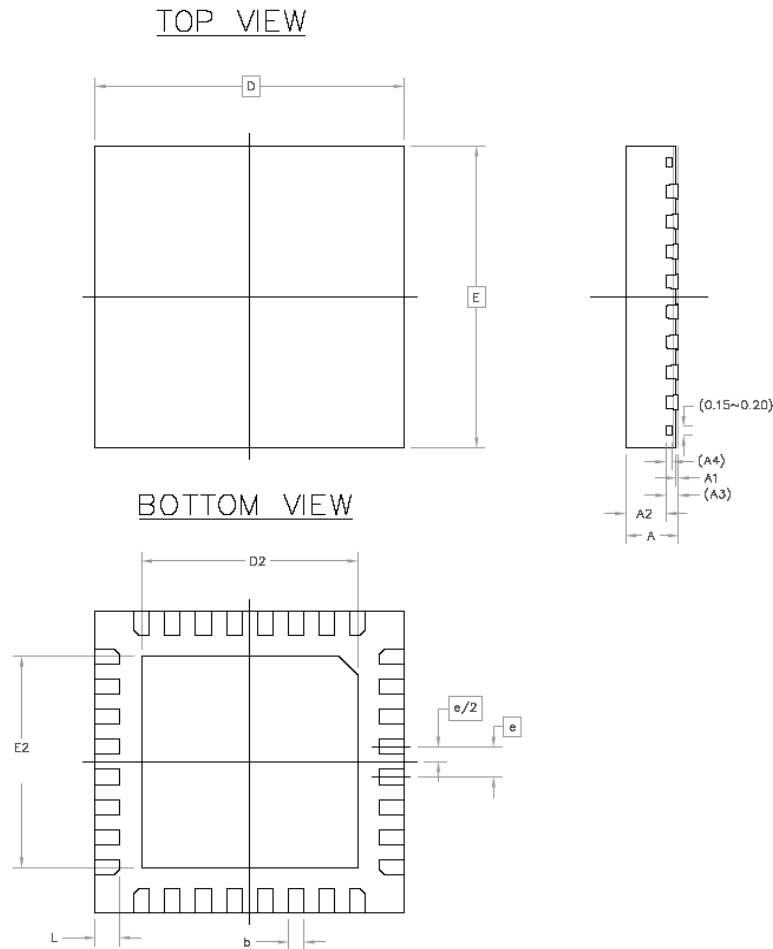
7.1.   Mechanical Dimensions Notes

Symbol	Dimension in mm			Dimension in inch		
	Min	**Nom**	**Max**	**Min**	**Nom**	**Max**
A	0.80	0.85	0.90	0.031	0.033	0.035
A1	0.00	0.02	0.05	0.000	0.001	0.002
A3	0.20 REF			0.008 REF		
A4	0.10 REF			0.004 REF		
b	0.18	0.25	0.30	0.007	0.010	0.012
D/E	5.00 BSC			0.020 BSC		
D2/E2	3.25	3.50	3.75	0.128	0.138	0.148
e	0.50 BSC			0.020 BSC		
L	0.30	0.40	0.50	0.012	0.016	0.020

Note 1: CONTROLLING DIMENSION: MILLIMETER (mm).
Note 2: REFERENCE DOCUMENT: JEDEC MO-220.

8. Ordering Information

Table 16. Ordering Information

Part Number	Package	Status
RTL8189ES-VB-CG	QFN-32, 'Green' Package	Mass Production

Note: See page 4 for package identification.

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